

FDMS86320 Information



For Reference Only

Part Number FDMS86320

ManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 80V 10.5A 8-PQFN

Package 8-PowerTDFN

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









FDMS86320 Specifications

Manufacturer Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-PowerTDFN Series PowerTrench? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 80V Current - Continuous Drain (Id) @ 25°C 10.5A (Ta), 22A (Tc) Drive Voltage (Max Rds On, Min Rds On) 8V, 10V Vgs(th) (Max) @ Id 4.5V @ 250µA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 2640pF @ 40V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11.7 mOhm @ 10.5A, 10V Operating Temperature Supplier Device Package Package / Case 8-PowerTDFN		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single 8-PowerTDFN Series PowerTrench? FET Type N-Channel Technology MOSFET (Metal Oxide) Porain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11.7 mOhm @ 10.5A, 10V Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case PowerTDFN	Manufacturer Part Number	FDMS86320
Package 8-PowerTDFN Series PowerTrench? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 80V Current - Continuous Drain (Id) @ 25°C 10.5A (Ta), 22A (Tc) Drive Voltage (Max Rds On, Min Rds On) 8V, 10V Vgs(th) (Max) @ Id 4.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 41nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2640pF @ 40V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.5W (Ta), 69W (Tc) Rds On (Max) @ Id, Vgs 11.7 mOhm @ 10.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-PQFN (5x6), Power56 Package / Case 8-PowerTDFN	Manufacturer	Fairchild/ON Semiconductor
Package 8-PowerTDFN Series PowerTrench? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 80V Current - Continuous Drain (Id) @ 25°C 10.5A (Ta), 22A (Tc) Drive Voltage (Max Rds On, Min Rds On) 8V, 10V Vgs(th) (Max) @ Id 4.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 41nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2640pF @ 40V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.5W (Ta), 69W (Tc) Rds On (Max) @ Id, Vgs 11.7 mOhm @ 10.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-PQFN (5x6), Power56 Package / Case 8-PowerTDFN	Category	Discrete Semiconductor Products
Series PowerTrench? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 80V Current - Continuous Drain (Id) @ 25°C 10.5A (Ta), 22A (Tc) Drive Voltage (Max Rds On, Min Rds On) 8V, 10V Vgs(th) (Max) @ Id 4.5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 41nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2640pF @ 40V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.5W (Ta), 69W (Tc) Rds On (Max) @ Id, Vgs 11.7 mOhm @ 10.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-PQFN (5x6), Power56 Package / Case 8-PowerTDFN		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)80VCurrent - Continuous Drain (Id) @ 25°C10.5A (Ta), 22A (Tc)Drive Voltage (Max Rds On, Min Rds On)8V, 10VVgs(th) (Max) @ Id4.5V @ 250μAGate Charge (Qg) (Max) @ Vgs41nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2640pF @ 40VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 69W (Tc)Rds On (Max) @ Id, Vgs11.7 mOhm @ 10.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-PQFN (5x6), Power56Package / Case8-PowerTDFN	Package	8-PowerTDFN
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11.7 mOhm @ 10.5A, 10V Operating Temperature Supplier Device Package Package / Case MOSFET (Metal Oxide) 80V 80V 80V 80V 10.5A (Ta), 22A (Tc) 10.5A (Ta) 24 (To) 10 (To) 11 (To) 11 (To) 11 (To) 12 (Ta) 13 (To) 14 (To) 15 (Ta) 16 (Ta) 17 (To) 18 (To) 18 (To) 19 (To) 19 (To) 10 (To) 10 (To) 11 (To) 11 (To) 12 (To) 13 (To) 14 (To) 15 (To) 16 (To) 17 (To) 18 (To) 18 (To) 19 (To) 19 (To) 10 (To) 10 (To) 10 (To) 10 (To) 11 (To) 11 (To) 12 (To) 13 (To) 14 (To) 15 (To) 16 (To) 17 (To) 18 (To	Series	PowerTrench?
Drain to Source Voltage (Vdss)80VCurrent - Continuous Drain (Id) @ 25°C10.5A (Ta), 22A (Tc)Drive Voltage (Max Rds On, Min Rds On)8V, 10VVgs(th) (Max) @ Id4.5V @ 250μAGate Charge (Qg) (Max) @ Vgs41nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2640pF @ 40VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 69W (Tc)Rds On (Max) @ Id, Vgs11.7 mOhm @ 10.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-PQFN (5x6), Power56Package / Case8-PowerTDFN	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 8V, 10V Vgs(th) (Max) @ Id 4.5V @ 250µA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11.7 mOhm @ 10.5A, 10V Operating Temperature Surplier Device Package Package / Case 10.5A (Ta), 22A (Tc)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11.7 mOhm @ 10.5A, 10V Operating Temperature Surplier Device Package Package / Case 8-POWEr TDFN	Drain to Source Voltage (Vdss)	80V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11.7 mOhm @ 10.5A, 10V Operating Temperature Surplier Device Package Package / Case 8-POWerTDFN	Current - Continuous Drain (Id) @ 25°C	10.5A (Ta), 22A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case 41nC @ 10V 2640pF @ 40V 2640pF @ 40V 250V 11.7 mOhm @ 10.5A, 10V 2.5W (Ta), 69W (Tc) 11.7 mOhm @ 10.5A, 10V Surface Mount Surface Mount 8-PQFN (5x6), Power56	Drive Voltage (Max Rds On, Min Rds On)	8V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11.7 mOhm @ 10.5A, 10V Operating Temperature Operating Type Surface Mount Supplier Device Package Package / Case 2640pF @ 40V 250V 11.7 mOhm @ 10.5A, 10V 11.7 mOhm @ 10.5A, 10V Surface Mount Surface Mount Supplier Device Package 8-POWerTDFN	Vgs(th) (Max) @ Id	4.5V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 69W (Tc)Rds On (Max) @ Id, Vgs11.7 mOhm @ 10.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-PQFN (5x6), Power56Package / Case8-PowerTDFN	Gate Charge (Qg) (Max) @ Vgs	41nC @ 10V
FET Feature Power Dissipation (Max) 2.5W (Ta), 69W (Tc) Rds On (Max) @ Id, Vgs 11.7 mOhm @ 10.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-PQFN (5x6), Power56 Package / Case 8-PowerTDFN	Input Capacitance (Ciss) (Max) @ Vds	2640pF @ 40V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11.7 mOhm @ 10.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-PQFN (5x6), Power56 Package / Case 8-PowerTDFN	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs11.7 mOhm @ 10.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-PQFN (5x6), Power56Package / Case8-PowerTDFN	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-PQFN (5x6), Power56 Package / Case 8-PowerTDFN	Power Dissipation (Max)	2.5W (Ta), 69W (Tc)
Mounting Type Surface Mount Supplier Device Package 8-PQFN (5x6), Power56 Package / Case 8-PowerTDFN	Rds On (Max) @ Id, Vgs	11.7 mOhm @ 10.5A, 10V
Supplier Device Package 8-PQFN (5x6), Power56 Package / Case 8-PowerTDFN	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 8-PowerTDFN	Mounting Type	Surface Mount
	Supplier Device Package	8-PQFN (5x6), Power56
Report errors?	Package / Case	8-PowerTDFN
Report crists:		Report errors?

FDMS86320 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

FDMS86320 Payment Methods





















FDMS86320 Shipping Methods













If you have any question about FDMS86320, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com